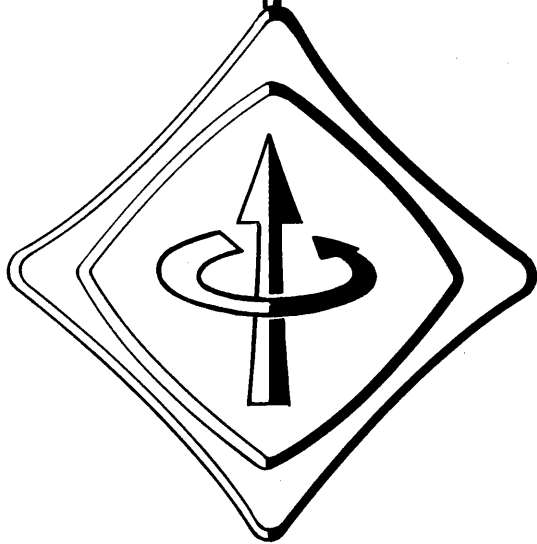


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## INTERNATIONAL RELIABILITY PHYSICS SYMPOSIUM AWARD

The International Reliability Physics Symposium Award for Outstanding Contributions in the Field of Reliability Physics was first authorized in 1971 by the Symposium Board of Directors. This award, which is not necessarily given annually, is presented to individuals who have made major significant contributions to the advancement of the field of reliability

The 1979 award was presented to D. Stewart Peck of the Bell Telephone Laboratories, Allentown, Pennsylvania, in recognition of his numerous contributions to the field of Reliability Physics. He was an early proponent of log-normal life distributions for semiconductor devices and a missionary for accelerated testing. These techniques are used by companies throughout the world and have become very important tools for quality control, for rapid evaluation of process changes, and for predicting the useful life of new products. His papers and tutorials given at the symposium have been models of technical excellence and clarity. His work on temperature-humidity acceleration of metal electrolysis failure in semiconductor devices is particularly notable. Mr. Peck has also given years of dedicated service to the symposium as a member of the Management Committee, as a member of the Board of Directors and as General Chairman of the symposium.



### INTERNATIONAL RELIABILITY PHYSICS AWARD PRESENTATION

D. Stewart Peck, award recipient (left)  
Jacob H. Martin, Chairman, Board of Directors (right)

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